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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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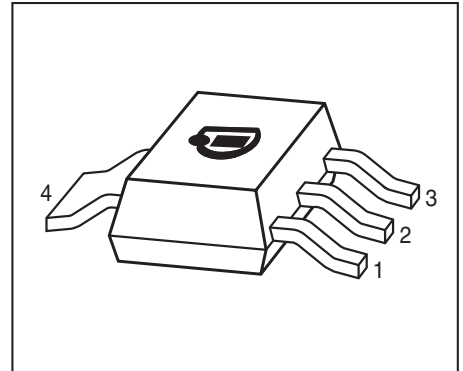
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Silicon NPN Transistors

- For AF driver and output stages
- High collector current
- High current gain
- Low collector-emitter saturation voltage
- Complementary types: BDP948, BDP950, BDP954 (PNP)
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



Type	Marking	Pin Configuration						Package
		1=B	2=C	3=E	4=C	-	-	
BDP947	BDP947	1=B	2=C	3=E	4=C	-	-	SOT223
BDP949	BDP949	1=B	2=C	3=E	4=C	-	-	SOT223
BDP953	BDP953	1=B	2=C	3=E	4=C	-	-	SOT223

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}		V
BDP947		45	
BDP949		60	
BDP953		100	
Collector-base voltage	V_{CBO}		
BDP947		45	
BDP949		60	
BDP953		120	
Emitter-base voltage	V_{EBO}	5	
Collector current	I_C	3	A
Peak collector current, $t_p \leq 10$ ms	I_{CM}	5	
Base current	I_B	200	mA
Peak base current, $t_p \leq 10$ ms	I_{BM}	500	
Total power dissipation- $T_S \leq 100$ °C	P_{tot}	5	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}	≤ 10	K/W

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 10\text{ mA}$, $I_B = 0$, BDP947 $I_C = 10\text{ mA}$, $I_B = 0$, BDP949 $I_C = 10\text{ mA}$, $I_B = 0$, BDP953	$V_{(BR)CEO}$	45 60 100	- - -	- - -	V
Collector-base breakdown voltage $I_C = 100\text{ }\mu\text{A}$, $I_E = 0$, BDP947 $I_C = 100\text{ }\mu\text{A}$, $I_E = 0$, BDP949 $I_C = 0$, $I_E = 100\text{ }\mu\text{A}$, BDP953	$V_{(BR)CBO}$	45 60 120	- - -	- - -	
Emitter-base breakdown voltage $I_E = 10\text{ }\mu\text{A}$, $I_C = 0$	$V_{(BR)EBO}$	5	-	-	
Collector-base cutoff current $V_{CB} = 45\text{ V}$, $I_E = 0$ $V_{CB} = 45\text{ V}$, $I_E = 0$, $T_A = 150\text{ }^\circ\text{C}$	I_{CBO}	- -	- -	0.1 20	μA
Emitter-base cutoff current $V_{EB} = 4\text{ V}$, $I_C = 0$	I_{EBO}	-	-	100	nA
DC current gain ²⁾ $I_C = 10\text{ mA}$, $V_{CE} = 5\text{ V}$ $I_C = 500\text{ mA}$, $V_{CE} = 1\text{ V}$ $I_C = 2\text{ A}$, $V_{CE} = 2\text{ V}$, BDP947, BDP949 $I_C = 2\text{ A}$, $V_{CE} = 2\text{ V}$, BDP953	h_{FE}	25 100 50 15	- - - -	- 475 - -	-
Collector-emitter saturation voltage ²⁾ $I_C = 2\text{ A}$, $I_B = 0.2\text{ A}$	V_{CEsat}	-	-	0.5	V
Base emitter saturation voltage ²⁾ $I_C = 2\text{ A}$, $I_B = 0.2\text{ A}$	V_{BEsat}	-	-	1.3	

AC Characteristics

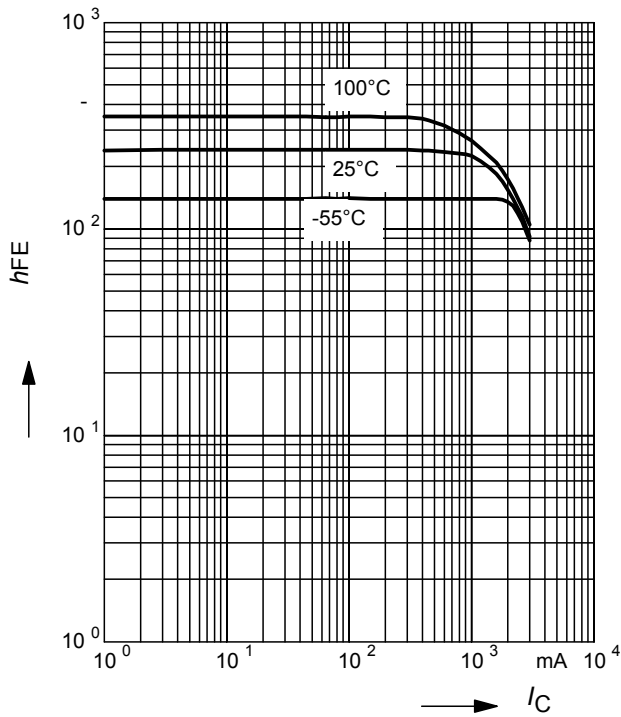
Transition frequency $I_C = 50\text{ mA}$, $V_{CE} = 10\text{ V}$, $f = 100\text{ MHz}$	f_T	-	100	-	MHz
Collector-base capacitance $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{cb}	-	25	-	pF

¹For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

²Pulse test: $t < 300\mu\text{s}$; $D < 2\%$

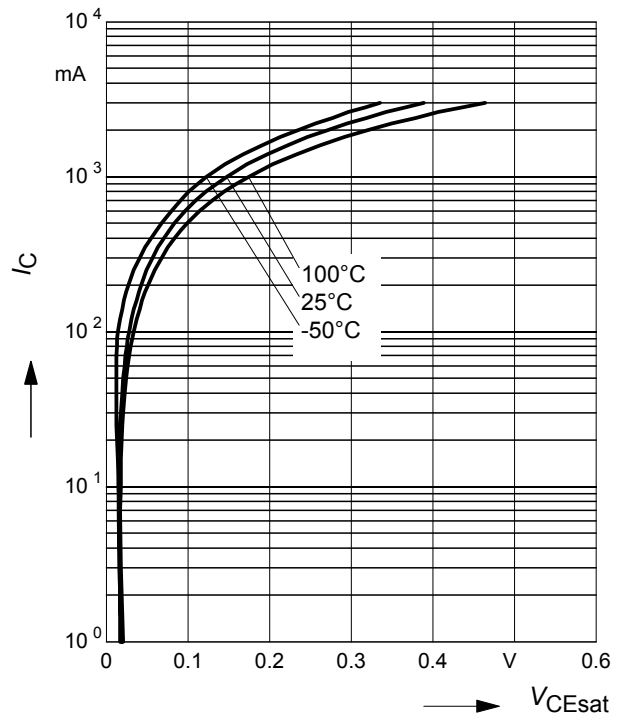
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 2\text{ V}$



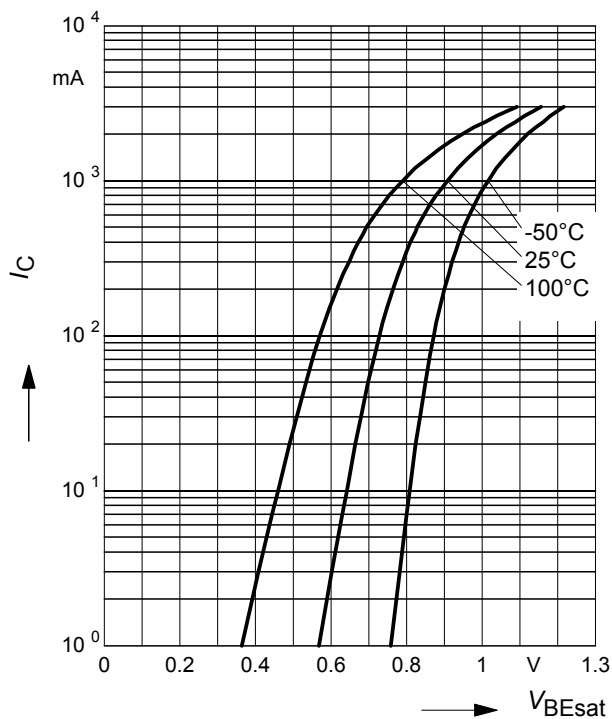
Collector-emitter saturation voltage

$I_C = f(V_{CEsat}), h_{FE} = 10$



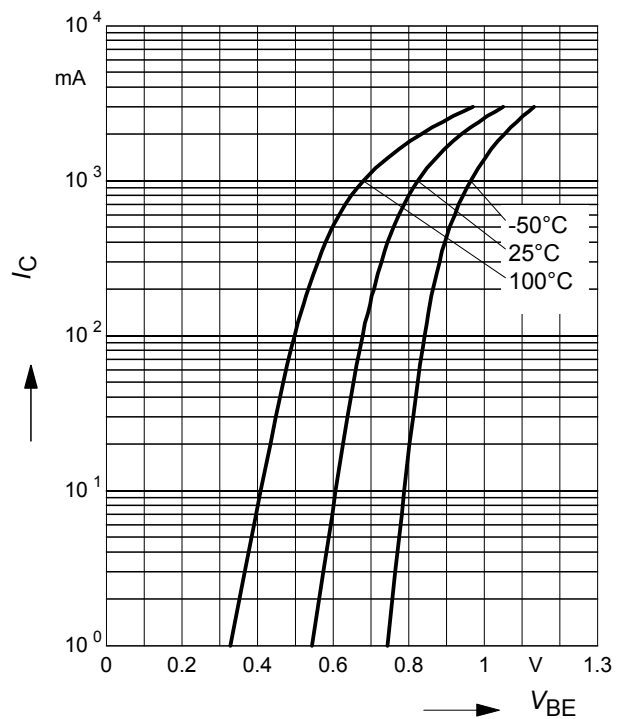
Base-emitter saturation voltage

$I_C = f(V_{BEsat}), h_{FE} = 10$



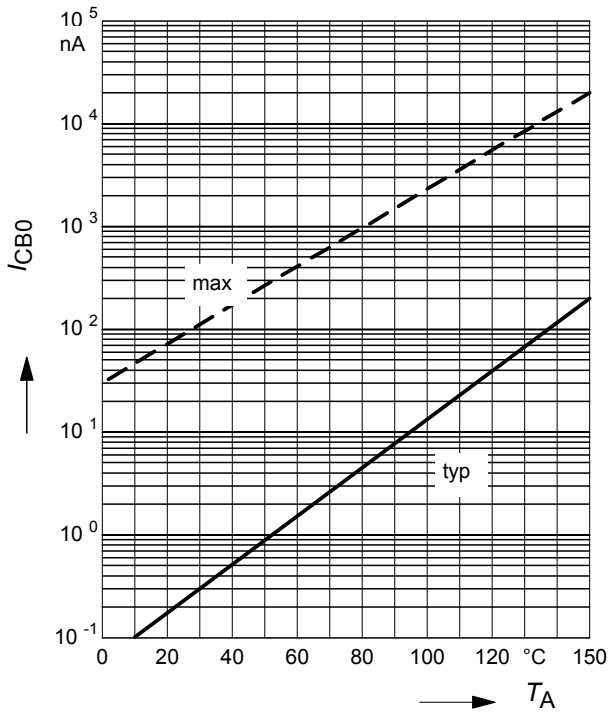
Collector current $I_C = f(V_{BE})$

$V_{CE} = 2\text{ V}$



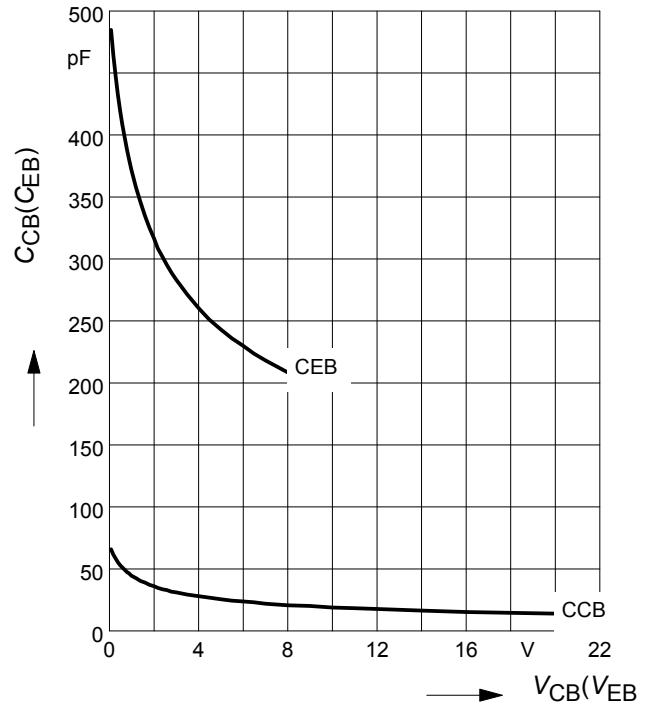
Collector cutoff current $I_{CBO} = f(T_A)$

$V_{CB} = 45\text{ V}$

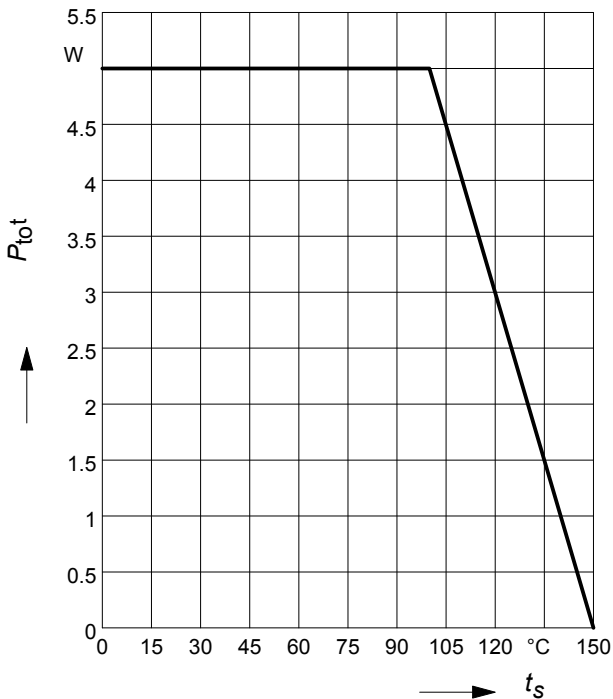


Collector-base capacitance $C_{cb} = f(V_{CB})$

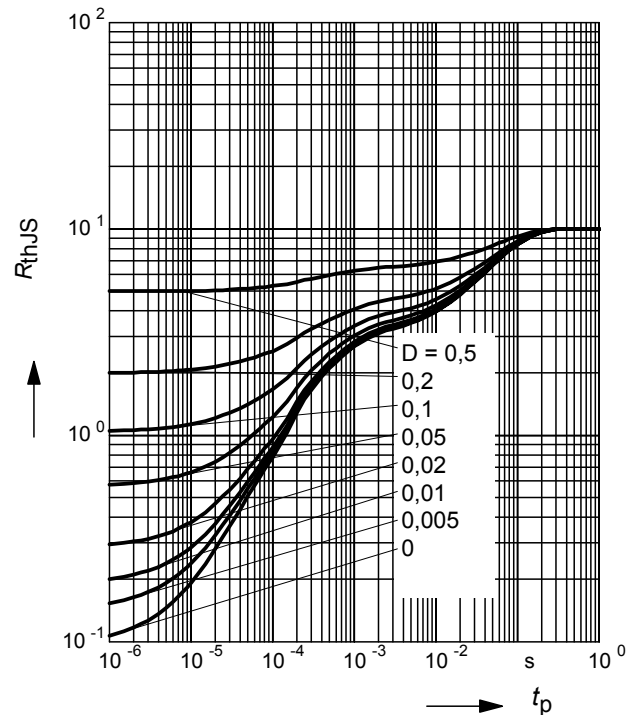
Emitter-base capacitance $C_{eb} = f(V_{EB})$



Total power dissipation $P_{tot} = f(T_S)$

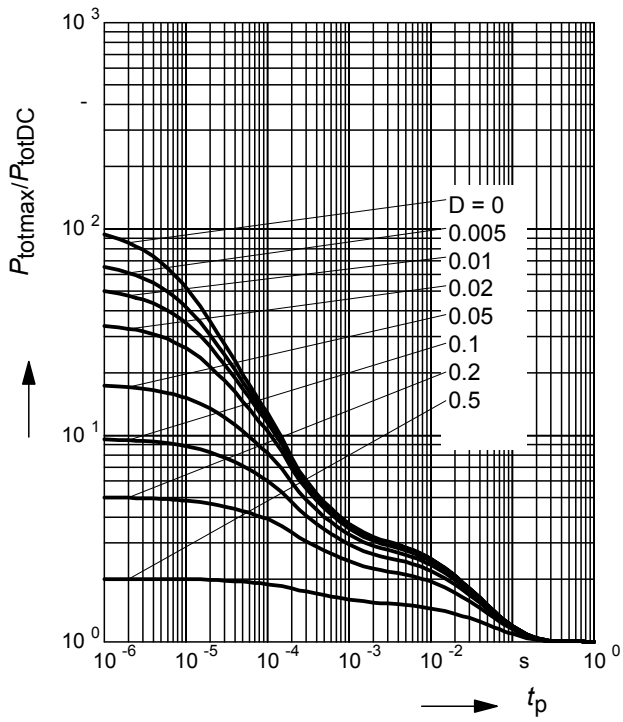


Permissible Pulse Load $R_{thJS} = f(t_p)$

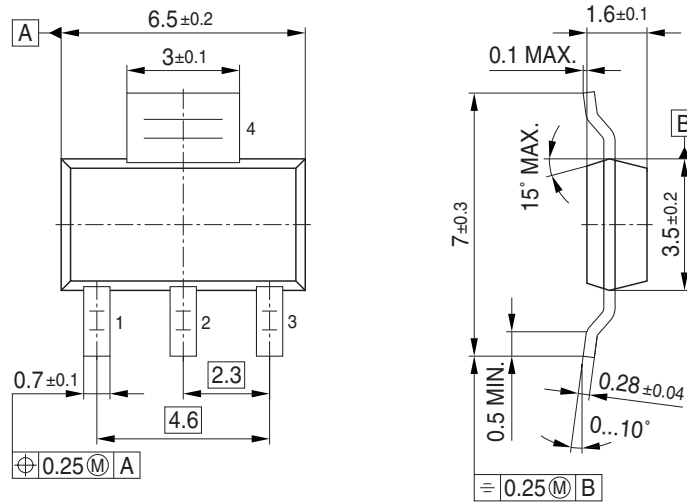
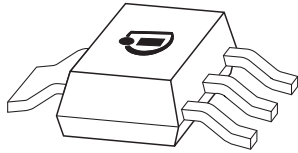


Permissible Pulse Load

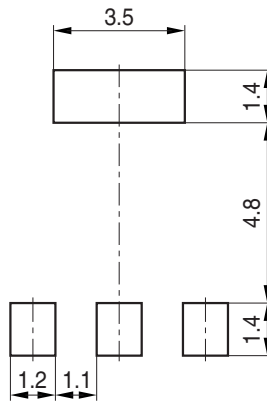
$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$$



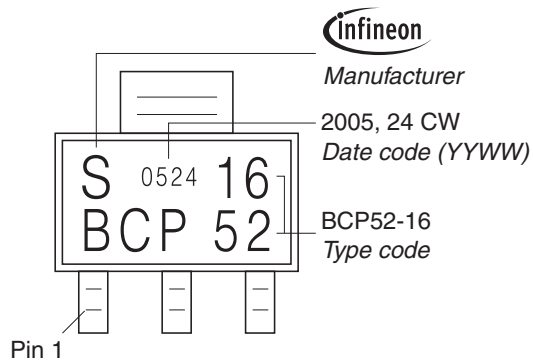
Package Outline



Foot Print

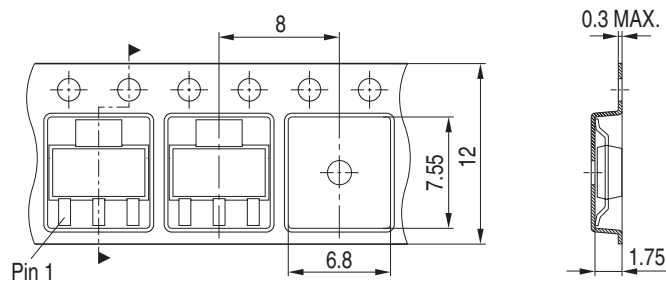


Marking Layout (Example)



Packing

Reel $\varnothing 180$ mm = 1.000 Pieces/Reel
 Reel $\varnothing 330$ mm = 4.000 Pieces/Reel



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